

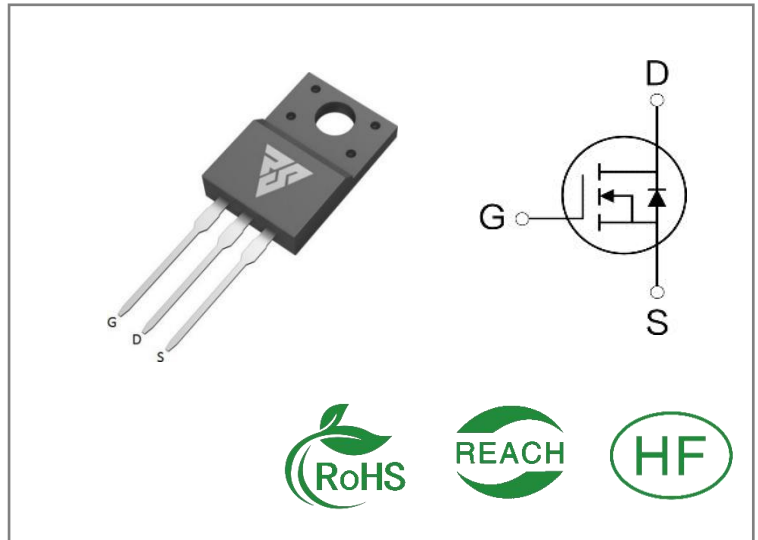
ID	R _{DS(ON)} (Typ)	VDSS
12A	0.5Ω	600V

Applications:

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Features:

- Fast switching speed
- 100% avalanche tested
- Improved dv/dt capability


Ordering Information

Part Number	Package	Marking	Packing	Qty.
RS12N60F	T0-220F	RS12N60F	Tube	50 PCS

Absolute Maximum Ratings T_c= 25°C unless otherwise specified

Symbol	Parameter	RS12N60F	Units
VDSS	Drain-to-Source Voltage	600	V
ID	Continuous Drain Current TC=25°C	12	A
IDM	Pulsed Drain Current (Note*1)	48	
PD	Power Dissipation	42	W
VGS	Gate- to- Source Voltage	±30	V
EAS	Single Pulse Avalanche Energy L = 10mH, VDD = 50V, RG = 25 Ω	450	mJ
TL TPKG	Maximum Temperature for Soldering	300 260	°C
	Leads at 0.063in(1.6mm)from Case for 10 seconds Package Body for 10 seconds		
TJ and TSTG	Operating Junction and Storage Temperature Range	-55 to 150	

* Drain Current Limited by Maximum Junction Temperature

Caution: Stresses greater than those listed in the“ Absolute Maximum Ratings” Table may cause permanent damage to the device.

Thermal Resistance

Symbol	Parameter	RS12N60F	Units	Test Conditions
R θ JC	Junction-to-Case	1.92	$^{\circ}\text{C} / \text{W}$	Drain lead soldered to water cooled heatsink, PD adjusted for a peak junction temperature of + 1 5 0 $^{\circ}\text{C}$
R θ JA	Junction-to-Ambient	62.5		1 cubic foot chamber, free air.

OFF Characteristics $T_J = 25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BVDSS	Drain- to- source Breakdown Voltage	600	--	--	V	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$
IDSS	Drain- to- Source Leakage Current	--	--	1	μA	$V_{DS}=600\text{V}, V_{GS}=0\text{V}$
IGSS	Gate- to- Source Forward Leakage	--	--	100	nA	$V_{GS}=30\text{V}, V_{DS}=0\text{V}$
	Gate- to- Source Reverse Leakage	--	--	-100		$V_{GS}=-30\text{V}, V_{DS}=0\text{V}$

ON Characteristics $T_J = 25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
RDS(on)	Static Drain- to- Source On-Resistance(Note*2)	--	0.5	0.62	Ω	$V_{GS}=10\text{V}, I_D=6\text{A}$
VGS(TH)	Gate Threshold Voltage	3	--	4	V	$V_{GS}=V_{DS}, I_D=250\mu\text{A}$

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
td(ON)	Turn- on Delay Time	--	46	--	nS	$V_{DS}=300\text{V}$ $I_D=12\text{A}$ $R_G=25\Omega$
trise	Rise Time	--	32	--		
td(OFF)	Turn- OFF Delay Time	--	212	--		
tfall	Fall Time	--	54	--		

Dynamic Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
Ciss	Input Capacitance	--	1703	--	pF	VGS=0V VDS=25V f=1.0MHz
Coss	Output Capacitance	--	162	--		
Crss	Reverse Transfer Capacitance	--	19	--		
Qg	Total Gate Charge	--	49	--	nC	VDS=400V ID=12A VGS=10V
Qgs	Gate- to- Source Charge	--	7.5	--		
Qgd	Gate-to-Drain(" Miller") Charge	--	23.5	--		

Source- Drain Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
IS	Continuous Source Current	--	--	12	A	Integral pn- diode in MOSFET
ISM	Maximum Pulsed Current	--	--	48	A	
VSD	Diode Forward Voltage	--	--	1.4	V	IS=6A,VGS=0V
trr	Reverse Recovery Time	--	616	--	nS	VGS=0V IS=12A,di/dt=100 A/μs
Qrr	Reverse Recovery Charge	--	3	--	μC	

Notes:

- * 1. Repetitive rating,pulse width limited by maximum junction temperature.
- * 2. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 1\%$

Typical Feature Curve

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

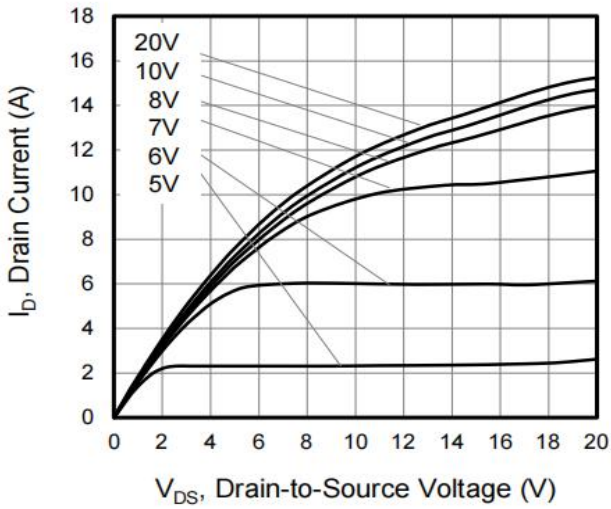


Figure 2. Body Diode Forward Voltage

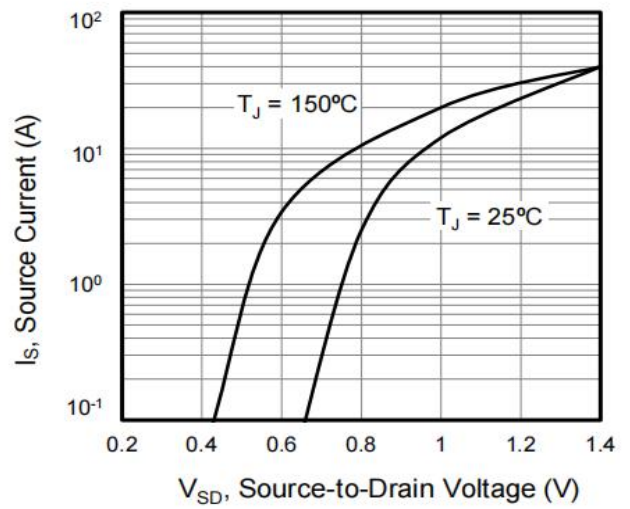


Figure 3. Drain Current vs. Temperature

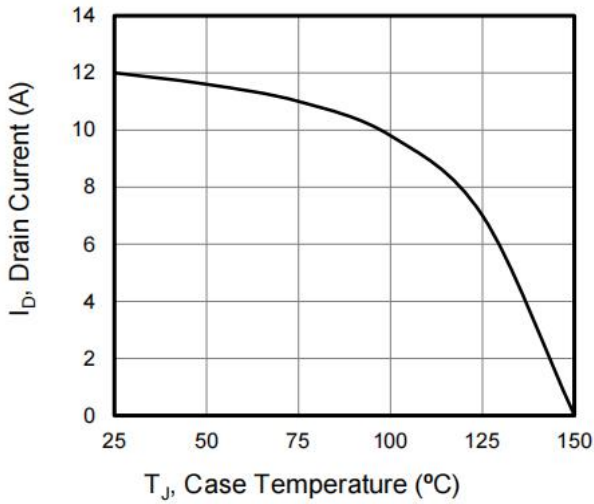


Figure 4. BV_{DSS} Variation vs. Temperature

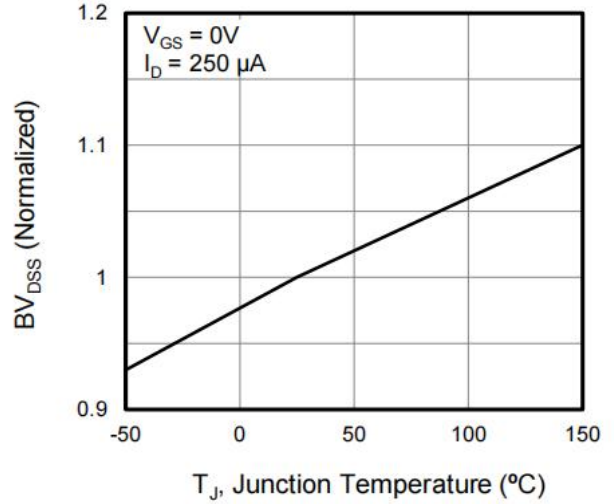


Figure 5. Transfer Characteristics

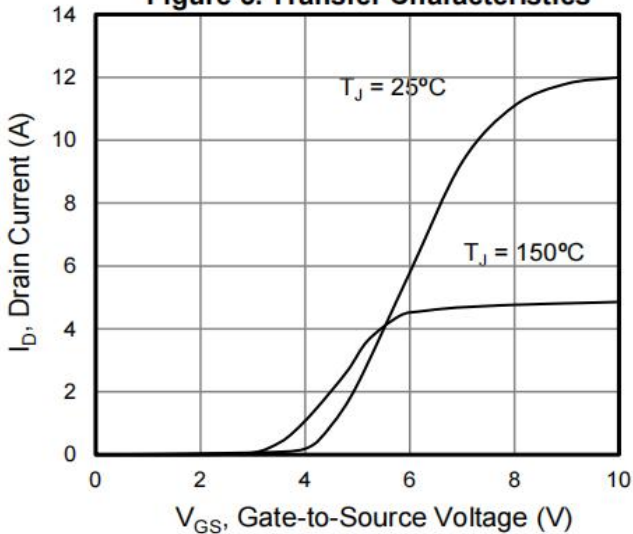


Figure 6. On-Resistance vs. Temperature

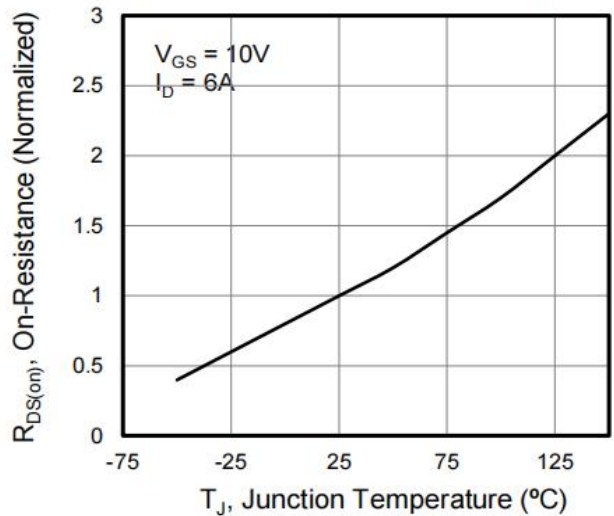


Figure 7. Capacitance

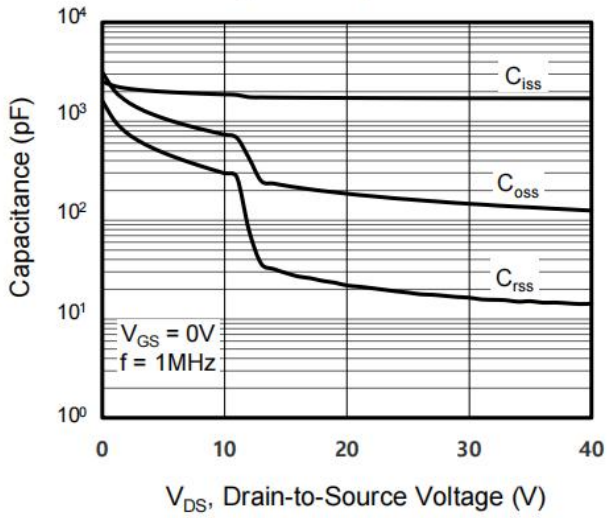


Figure 8. Gate Charge

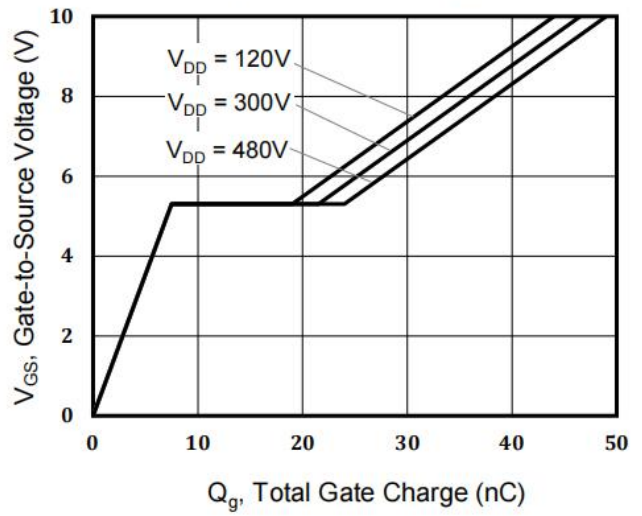
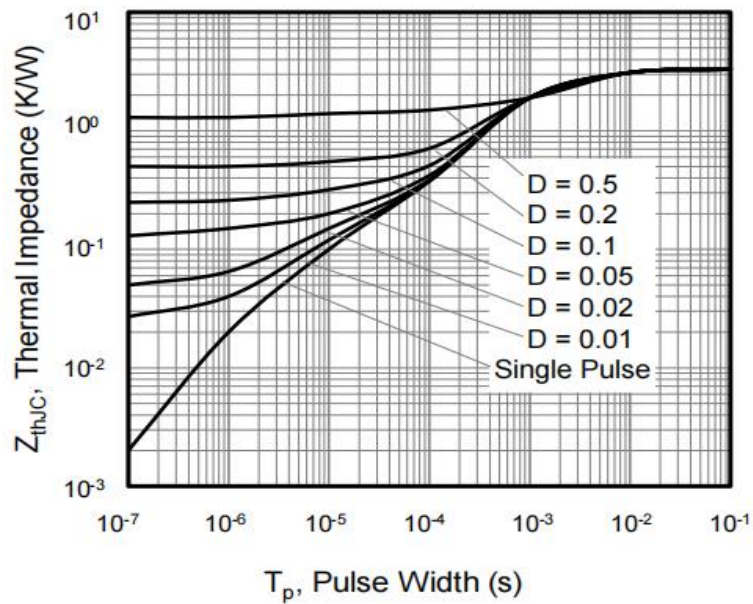


Figure 9. Transient Thermal Impedance



Test Circuits and Waveforms

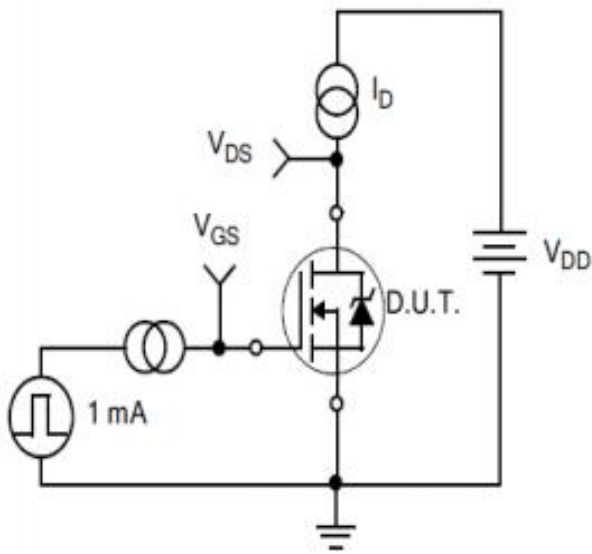


Figure 10.
Gate Charge Test Circuit

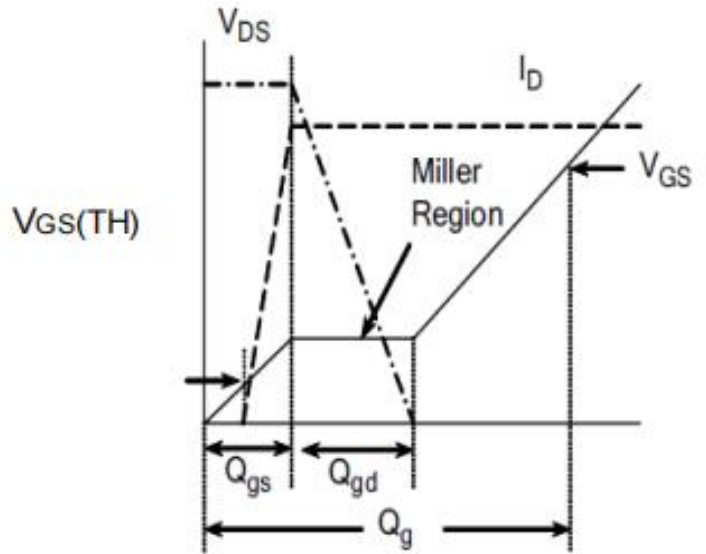


Figure 11.
Gate Charge Waveform

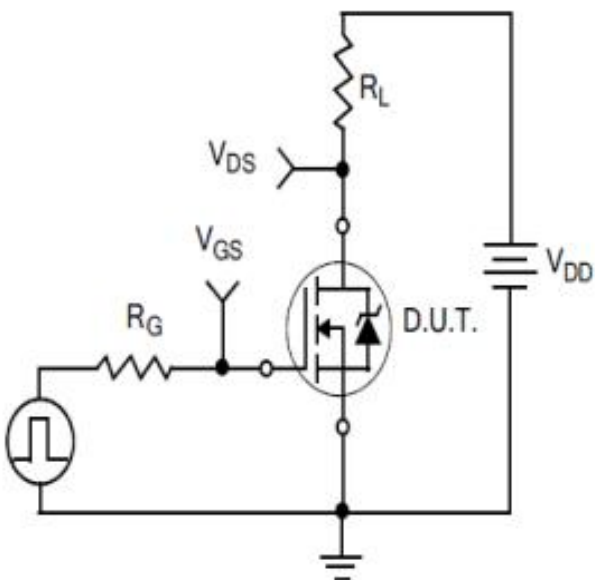


Figure 12.
Resistive Switching Test Circuit

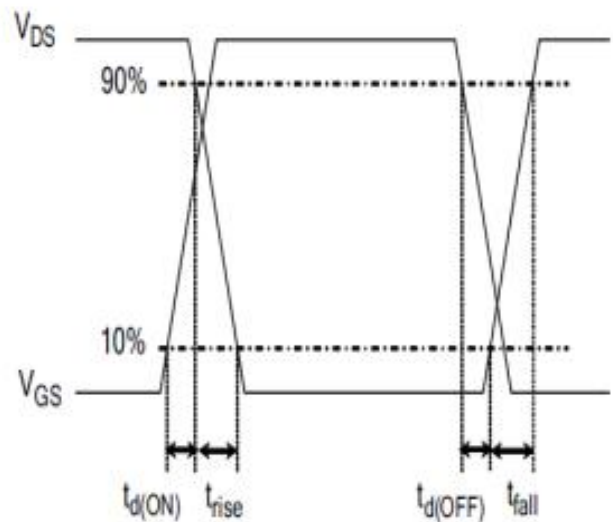


Figure 13.
Resistive Switching Waveforms

Test Circuits and Waveforms

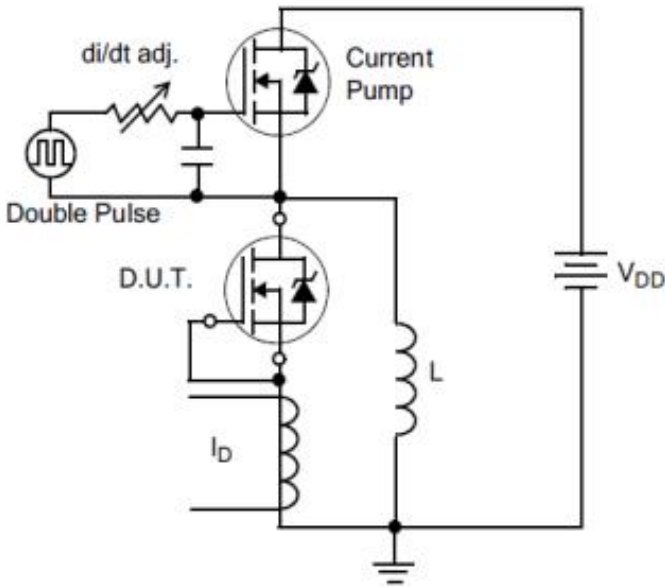


Figure 14. Diode Reverse Recovery Test Circuit

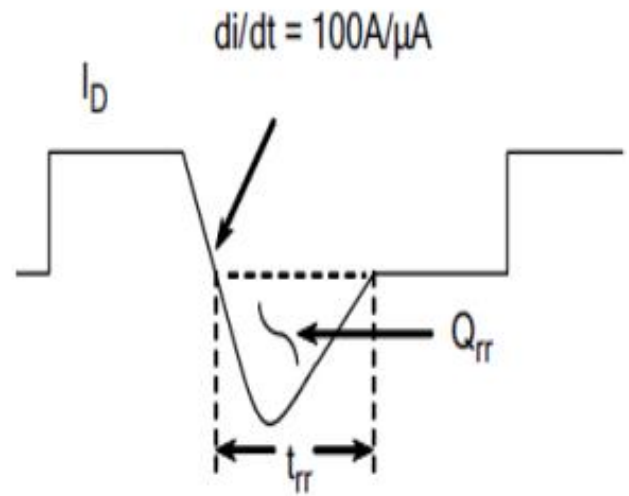


Figure 15. Diode Reverse Recovery Waveform

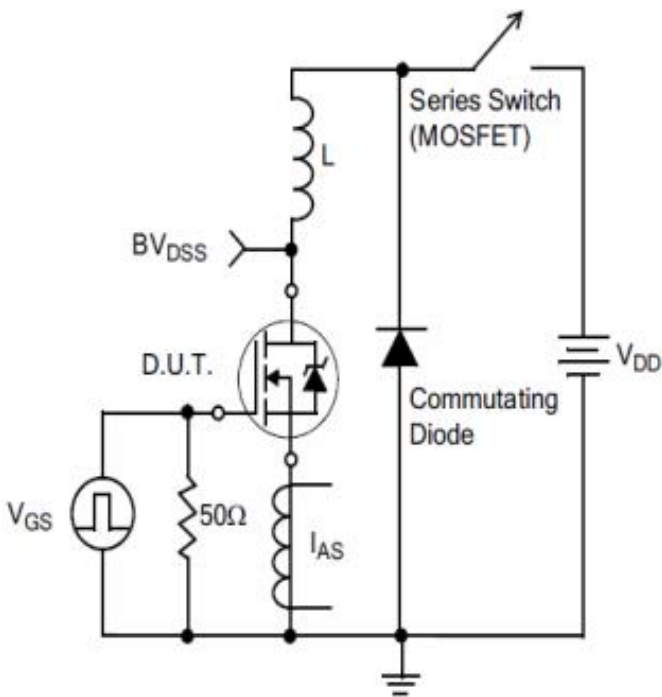
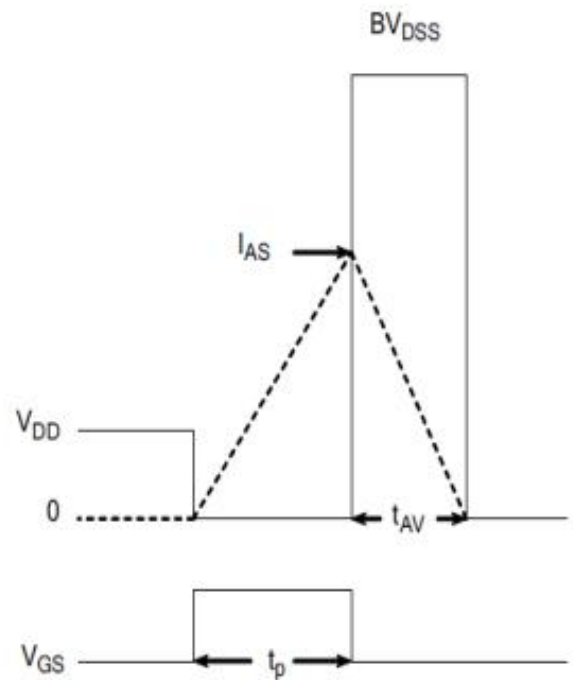


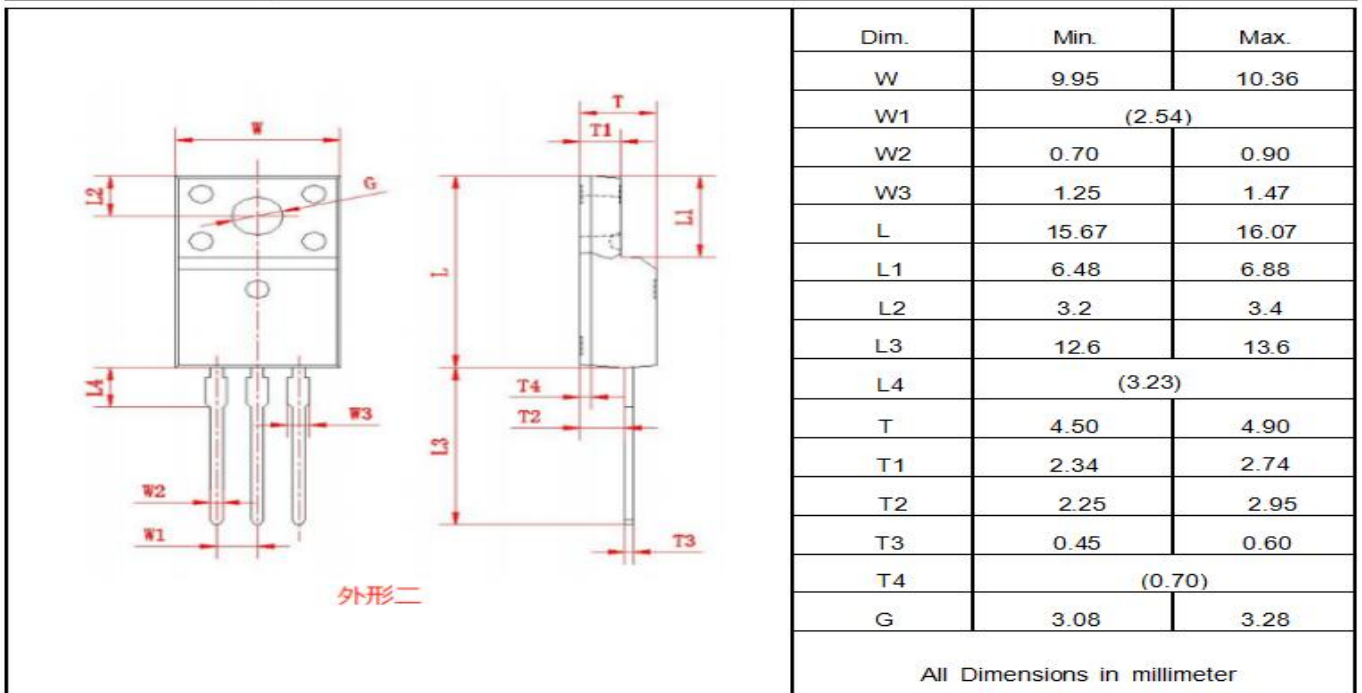
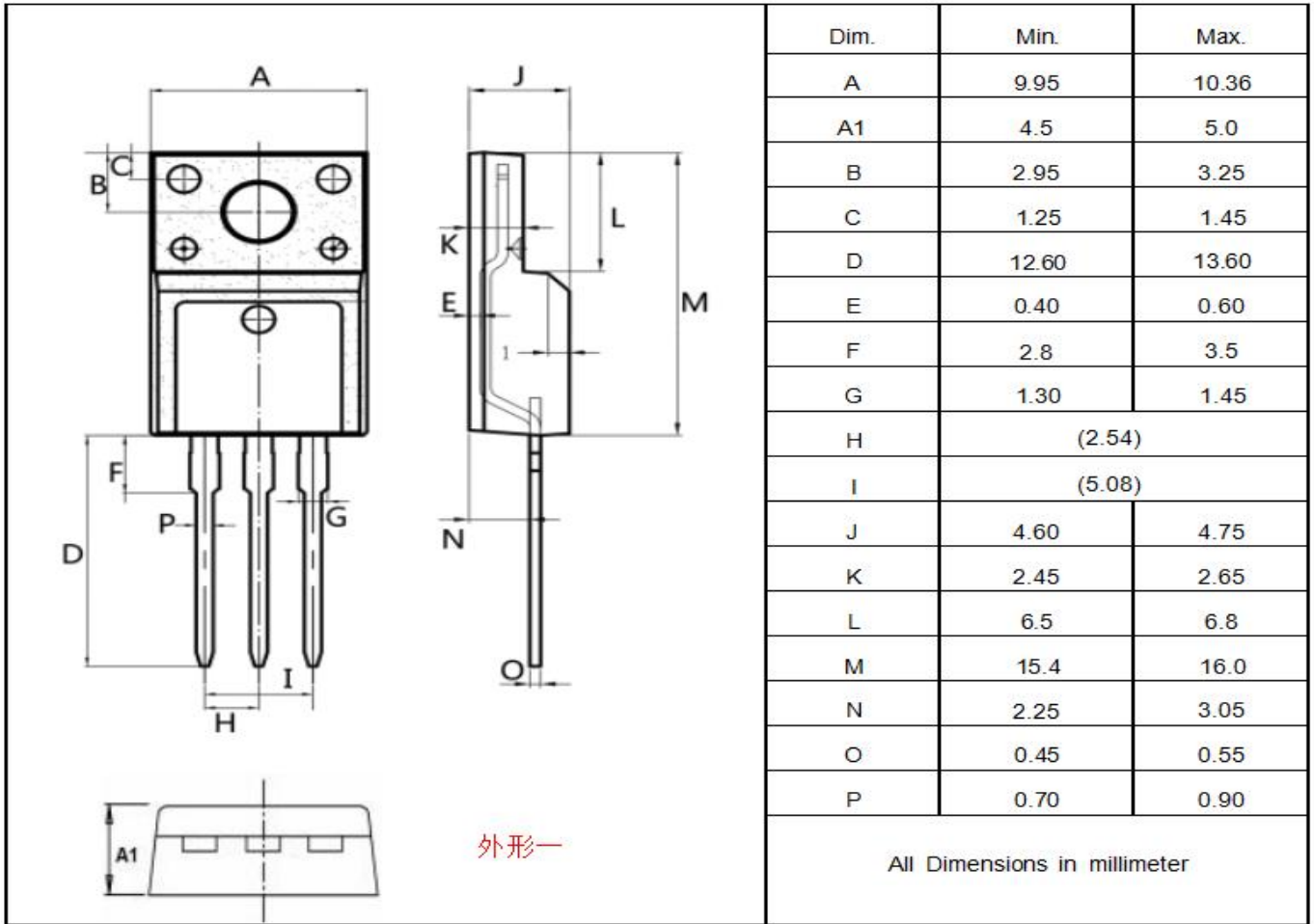
Figure 16. Unclamped Inductive Switching Test Circuit



$$E_{AS} = \frac{I_{AS}^2 L}{2}$$

Figure 17. Unclamped Inductive Switching Waveforms

Package outline drawing(TO-220F Unit: mm)



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